



SGM2267

0.4Ω Ultra Low ON-Resistance, Dual, SPDT Analog Switch

GENERAL DESCRIPTION

The SGM2267 is a dual single-pole/double-throw (SPDT) analog switch that is designed to operate from a single +1.8V to +4.2V power supply. Targeted applications include battery powered equipment that benefit from ultra low on-resistance (0.4Ω) and fast switching speeds.

SGM2267 features guaranteed on-resistance matching (0.04Ω TYP) between switches and guaranteed on-resistance flatness over the signal range (0.08Ω TYP), as well as high off-isolation and low crosstalk. This ensures excellent linearity and low distortion when switching audio signals.

The SGM2267 is a committed dual single-pole/double-throw (SPDT) that consist of two normally open (NO) and two normally close (NC) switches. This configuration can be used as a dual 2-to-1 multiplexer.

SGM2267 is available in Green TQFN-2.1×1.6-10L package.

FEATURES

- **Voltage Operation:** +1.8V to +4.2V
- **Ultra Low On-Resistance:** 0.4Ω (TYP) at +4.2V
- **On-Resistance Matching:** 0.04Ω (TYP)
- **On-Resistance Flatness:** 0.08Ω (TYP)
- **-3dB Bandwidth:** 40MHz
- **High Off-Isolation:** -78dB at 100kHz
- **Low Crosstalk:** -103dB at 100kHz
- **Rail-to-Rail Input and Output Operation**
- **TTL/CMOS Compatible**
- **Break-Before-Make Switching**
- **Extended Industrial Temperature Range:**
-40°C to +85°C
- **Available in Green TQFN-2.1×1.6-10L Package**

APPLICATIONS

Portable Instrumentation
Battery-Operated Equipment
Computer Peripherals
Speaker and Earphone Switching
Medical Equipment
Audio and Video Switching

PACKAGE/ORDERING INFORMATION

MODEL	PIN-PACKAGE	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKAGE OPTION
SGM2267	TQFN-2.1×1.6-10L	-40°C to +85°C	SGM2267YTQD10/TR	2267	Tape and Reel, 3000

ABSOLUTE MAXIMUM RATINGS

V₊, IN to GND.....0V to 4.6V
 Analog, Digital voltage range ⁽¹⁾..... -0.3V to (V₊) + 0.3V
 Continuous Current NO, NC, or COM.....±250mA
 Peak Current NO, NC, or COM.....±350mA
 Operating Temperature Range.....-40°C to +85°C
 Junction Temperature.....150°C
 Storage Temperature Range.....-65°C to +150°C
 Lead Temperature (soldering, 10s).....260°C
 ESD Susceptibility
 HBM.....4000V
 MM.....400V

NOTES:

1. Signals on NC, NO, or COM or IN exceeding V₊ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

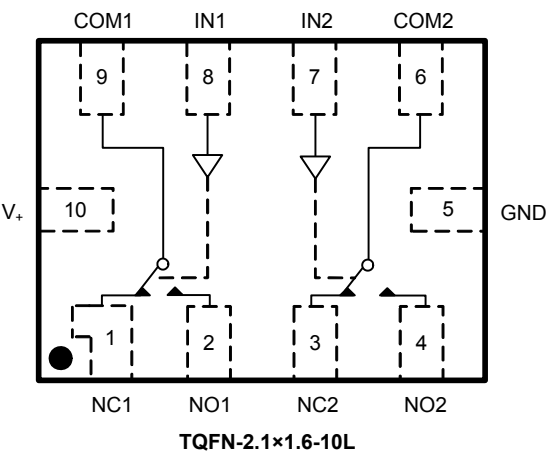
2. Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

SGMICRO reserves the right to make any change in circuit design, specification or other related things if necessary without notice at any time. Please contact SGMICRO sales office to get the latest datasheet.

PIN CONFIGURATION (TOP VIEW)



PIN DESCRIPTION

PIN	NAME	FUNCTION
10	V ₊	Power Supply.
5	GND	Ground.
8, 7	IN1, IN2	Digital Control Pin to Connect the COM Terminal to the NO or NC Terminals.
9, 6	COM1, COM2	Common Terminal.
2, 4	NO1, NO2	Normally-Open Terminal.
1, 3	NC1, NC2	Normally-Closed Terminal.

NOTE: NO, NC and COM terminals may be an input or output.

FUNCTION TABLE

LOGIC	NO	NC
0	OFF	ON
1	ON	OFF

Switches Shown For Logic “0” Input

ELECTRICAL CHARACTERISTICS

($V_+ = +4.2V$, $GND = 0V$, $V_{IH} = +1.6V$, $V_{IL} = +0.6V$, $T_A = -40^\circ C$ to $+85^\circ C$. Typical values are at $V_+ = +4.2V$, $T_A = +25^\circ C$, unless otherwise noted.)

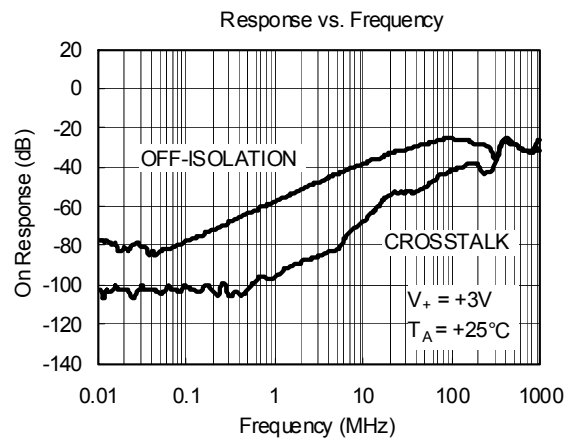
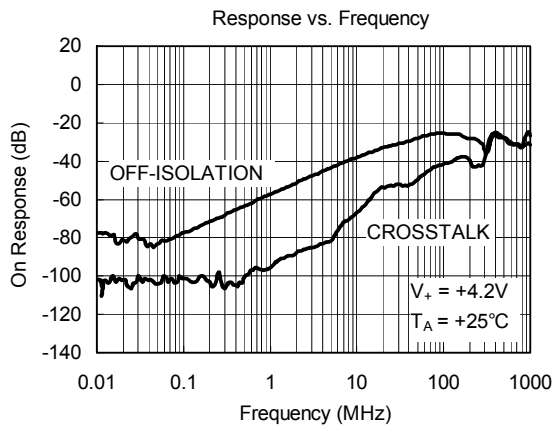
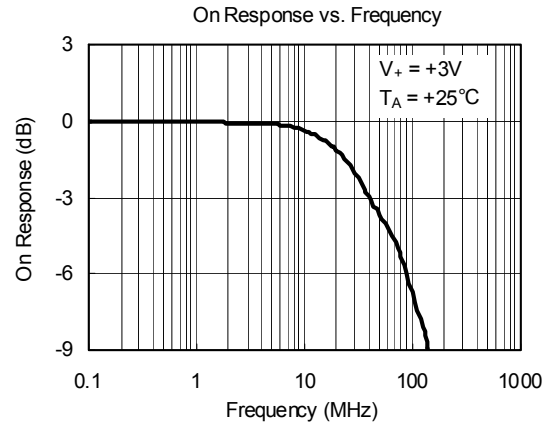
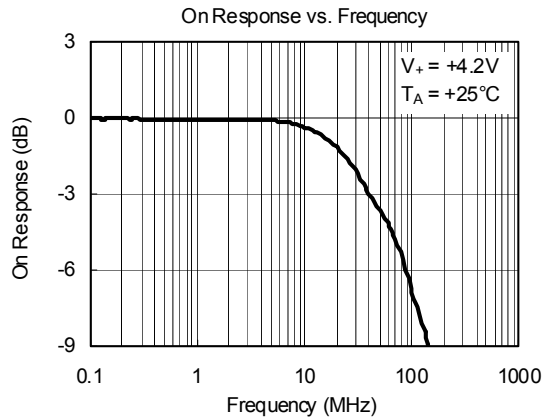
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V_{NO}, V_{NC}, V_{COM}		$-40^\circ C$ to $+85^\circ C$	0		V_+	V
On-Resistance	R_{ON}	$V_+ = 4.2V$, $0V \leq V_{NO}$ or $V_{NC} \leq V_+$, $I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.4	0.65	Ω
			$-40^\circ C$ to $+85^\circ C$			0.75	Ω
On-Resistance Match Between Channels	ΔR_{ON}	$V_+ = 4.2V$, $0V \leq V_{NO}$ or $V_{NC} \leq V_+$, $I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.04	0.15	Ω
			$-40^\circ C$ to $+85^\circ C$			0.2	Ω
On-Resistance Flatness	$R_{FLAT(ON)}$	$V_+ = 4.2V$, $0V \leq V_{NO}$ or $V_{NC} \leq V_+$, $I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.08	0.12	Ω
			$-40^\circ C$ to $+85^\circ C$			0.2	Ω
Source OFF Leakage Current	$I_{NC(OFF)}, I_{NO(OFF)}$	$V_+ = 4.2V$, V_{NO} or $V_{NC} = 3.3V/0.3V$, $V_{COM} = 0.3V/3.3V$	$-40^\circ C$ to $+85^\circ C$			1	μA
Channel ON Leakage Current	$I_{NC(ON)}, I_{NO(ON)}, I_{COM(ON)}$	$V_+ = 4.2V$, $V_{COM} = 0.3V/3.3V$, V_{NO} or $V_{NC} = 0.3V/3.3V$ or floating	$-40^\circ C$ to $+85^\circ C$			1	μA
DIGITAL INPUTS							
Input High Voltage	V_{INH}		$-40^\circ C$ to $+85^\circ C$	1.6			V
Input Low Voltage	V_{INL}		$-40^\circ C$ to $+85^\circ C$			0.5	V
Input Leakage Current	I_{IN}	$V_+ = 4.2V$, $V_{IN} = 0V$ or $4.2V$	$-40^\circ C$ to $+85^\circ C$			1	μA
DYNAMIC CHARACTERISTICS							
Turn-On Time	t_{ON}	$V_{IN} = 2.1V$ to $0V$, $R_L = 50\Omega$, $C_L = 35pF$, V_{NO1} or $V_{NC1} = V_{NO2}$ or $V_{NC2} = 2.1V$, Test Circuit 2	$+25^\circ C$		96		ns
Turn-Off Time	t_{OFF}	$V_{IN} = 2.1V$ to $0V$, $R_L = 50\Omega$, $C_L = 35pF$, V_{NO1} or $V_{NC1} = V_{NO2}$ or $V_{NC2} = 2.1V$, Test Circuit 2	$+25^\circ C$		16		ns
Break-Before-Make Time Delay	t_D	$V_{IN} = 2.1V$ to $0V$, $R_L = 50\Omega$, $C_L = 35pF$, V_{NO1} or $V_{NC1} = V_{NO2}$ or $V_{NC2} = 2.1V$, Test Circuit 3	$+25^\circ C$		25		ns
Off Isolation	O_{ISO}	$R_L = 50\Omega$, Signal = $0dBm$, Test Circuit 4	100kHz $+25^\circ C$		-78		dB
			1MHz $+25^\circ C$		-58		dB
Channel-to-Channel Crosstalk	X_{TALK}	$R_L = 50\Omega$, Signal = $0dBm$, Test Circuit 5	100kHz $+25^\circ C$		-103		dB
			1MHz $+25^\circ C$		-90		dB
-3dB Bandwidth	BW	$R_L = 50\Omega$, Signal = $0dBm$, Test Circuit 6	$+25^\circ C$		40.0		MHz
Charge Injection Select Input to Common I/O	Q	V_{NO1} or $V_{NC1} = V_{NO2}$ or $V_{NC2} = 0V$, $C_L = 1.0nF$, $R_S = 0\Omega$, Test Circuit 7	$+25^\circ C$		4.0		pC
Total Harmonic Distortion + Noise	THD+N	$V_{COM} = 2V_{P-P}$, $f = 20Hz$ to $20kHz$, Test Circuit 8	$+25^\circ C$		0.011		%
Channel ON Capacitance	C_{ON}		$+25^\circ C$		106		pF
POWER REQUIREMENTS							
Power Supply Range	V_+		$-40^\circ C$ to $+85^\circ C$	1.8		4.2	V
Power Supply Current	I_+	$V_+ = 4.2V$, $V_{IN} = 0V$ or V_+	$-40^\circ C$ to $+85^\circ C$			1	μA

ELECTRICAL CHARACTERISTICS

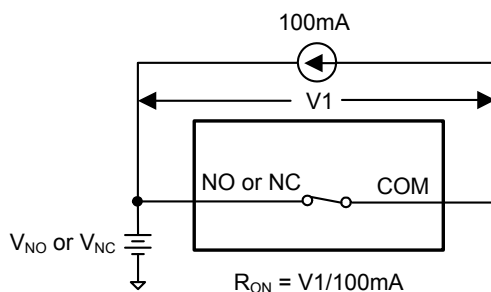
($V_+ = +2.7V$ to $+3.6V$, $GND = 0V$, $V_{IH} = +1.6V$, $V_{IL} = +0.4V$, $T_A = -40^\circ C$ to $+85^\circ C$. Typical values are at $V_+ = +3.0V$, $T_A = +25^\circ C$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V_{NO}, V_{NC}, V_{COM}		$-40^\circ C$ to $+85^\circ C$	0		V_+	V
On-Resistance	R_{ON}	$V_+ = 2.7V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.5	0.7	Ω
			$-40^\circ C$ to $+85^\circ C$			0.8	Ω
On-Resistance Match Between Channels	ΔR_{ON}	$V_+ = 2.7V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.03	0.15	Ω
			$-40^\circ C$ to $+85^\circ C$			0.2	Ω
On-Resistance Flatness	$R_{FLAT(ON)}$	$V_+ = 2.7V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.1	0.18	Ω
			$-40^\circ C$ to $+85^\circ C$			0.2	Ω
Source OFF Leakage Current	$I_{NC(OFF)}, I_{NO(OFF)}$	$V_+ = 3.6V, V_{NO} \text{ or } V_{NC} = 3.3V/0.3V, V_{COM} = 0.3V/3.3V$	$-40^\circ C$ to $+85^\circ C$			1	μA
Channel ON Leakage Current	$I_{NC(ON)}, I_{NO(ON)}, I_{COM(ON)}$	$V_+ = 3.6V, V_{COM} = 0.3V/3.3V, V_{NO} \text{ or } V_{NC} = 0.3V/3.3V$ or floating	$-40^\circ C$ to $+85^\circ C$			1	μA
DIGITAL INPUTS							
Input High Voltage	V_{INH}		$-40^\circ C$ to $+85^\circ C$	1.5			V
Input Low Voltage	V_{INL}		$-40^\circ C$ to $+85^\circ C$			0.4	V
Input Leakage Current	I_{IN}	$V_+ = 2.7V, V_{IN} = 0V$ or $2.7V$	$-40^\circ C$ to $+85^\circ C$			1	μA
DYNAMIC CHARACTERISTICS							
Turn-On Time	t_{ON}	$V_{IN} = 1.5V$ to $0V, R_L = 50\Omega, C_L = 35pF, V_{NO1} \text{ or } V_{NC1} = V_{NO2} \text{ or } V_{NC2} = 1.5V$, Test Circuit 2	$+25^\circ C$		100		ns
Turn-Off Time	t_{OFF}	$V_{IN} = 1.5V$ to $0V, R_L = 50\Omega, C_L = 35pF, V_{NO1} \text{ or } V_{NC1} = V_{NO2} \text{ or } V_{NC2} = 1.5V$, Test Circuit 2	$+25^\circ C$		25		ns
Break-Before-Make Time Delay	t_D	$V_{IN} = 1.5V$ to $0V, R_L = 50\Omega, C_L = 35pF, V_{NO1} \text{ or } V_{NC1} = V_{NO2} \text{ or } V_{NC2} = 1.5V$, Test Circuit 3	$+25^\circ C$		28		ns
Off Isolation	O_{ISO}	$R_L = 50\Omega$, Signal = $0dBm$, Test Circuit 4	100kHz	$+25^\circ C$		-78	dB
			1MHz	$+25^\circ C$		-58	dB
Channel-to-Channel Crosstalk	X_{TALK}	$R_L = 50\Omega$, Signal = $0dBm$, Test Circuit 5	100kHz	$+25^\circ C$		-103	dB
			1MHz	$+25^\circ C$		-90	dB
-3dB Bandwidth	BW	$R_L = 50\Omega$, Signal = $0dBm$, Test Circuit 6	$+25^\circ C$		40		MHz
Charge Injection Select Input to Common I/O	Q	$V_{NO1} \text{ or } V_{NC1} = V_{NO2} \text{ or } V_{NC2} = 0V, C_L = 1.0nF, R_S = 0\Omega$, Test Circuit 7	$+25^\circ C$		4.0		pC
Total Harmonic Distortion + Noise	THD+N	$V_{COM} = 1.5V_{P-P}, f = 20Hz$ to $20kHz$, Test Circuit 8	$+25^\circ C$		0.015		%
Channel ON Capacitance	C_{ON}		$+25^\circ C$		106		pF

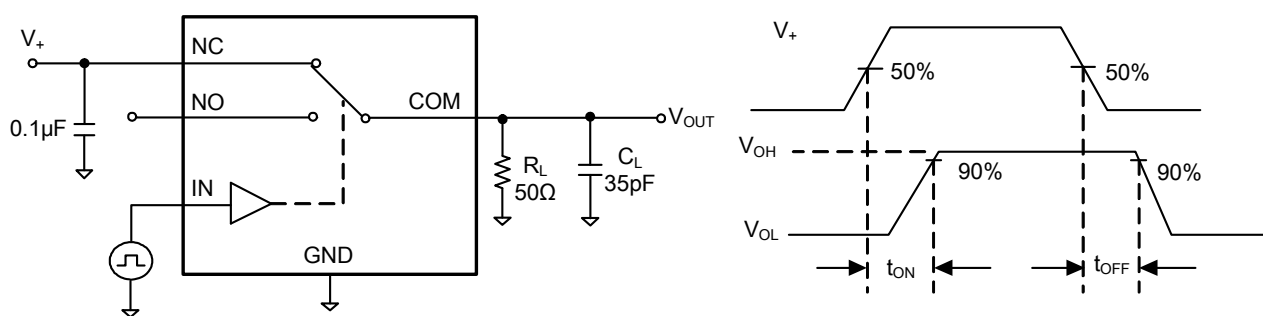
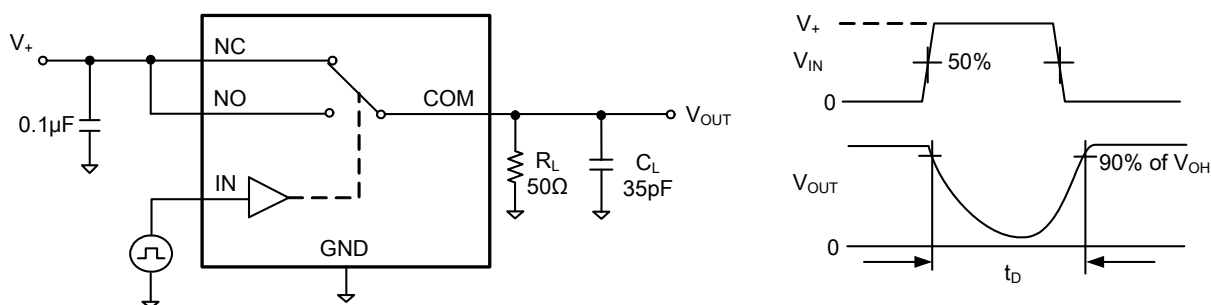
TYPICAL PERFORMANCE CHARACTERISTICS



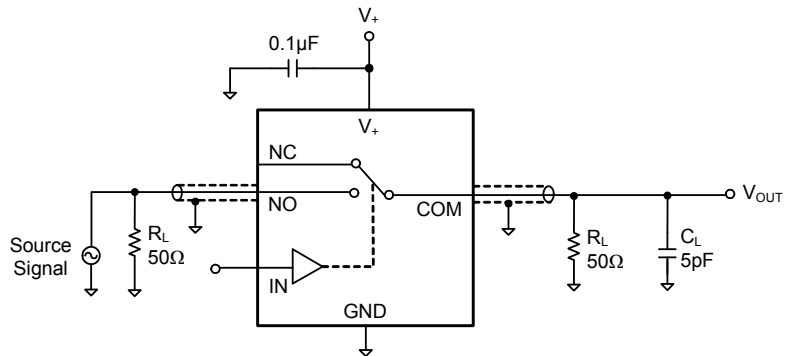
TEST CIRCUITS



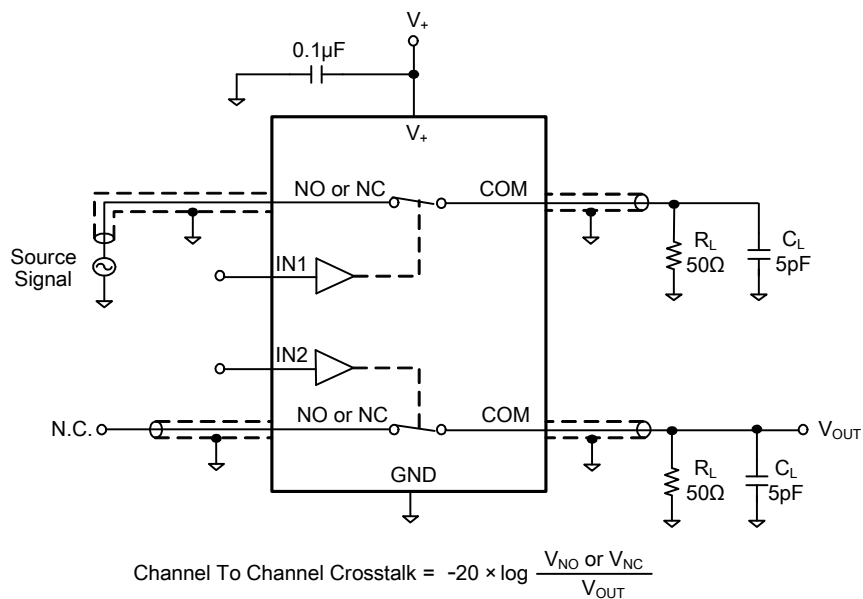
Test Circuit 1. On Resistance

Test Circuit 2. Switching Times (t_{ON} , t_{OFF})Test Circuit 3. Break-Before-Make Time (t_D)

TEST CIRCUITS (Cont.)

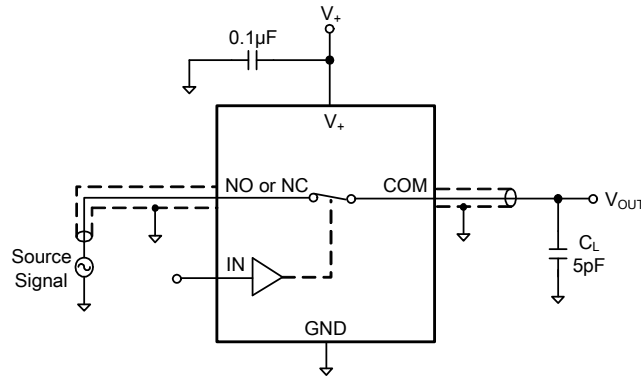


Test Circuit 4. Off Isolation

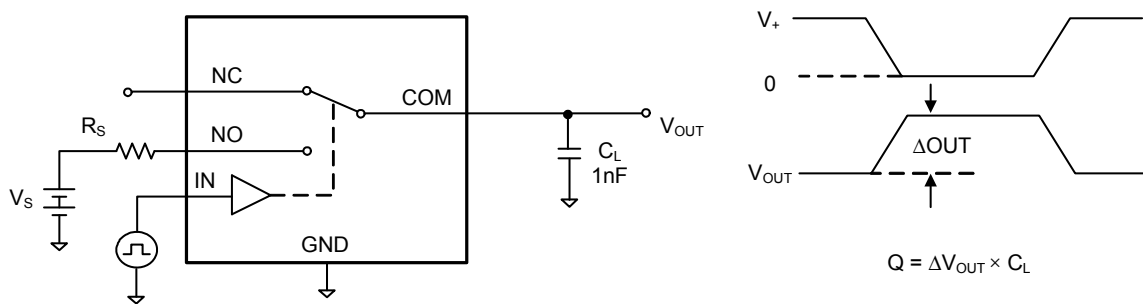


Test Circuit 5. Channel-to-Channel Crosstalk

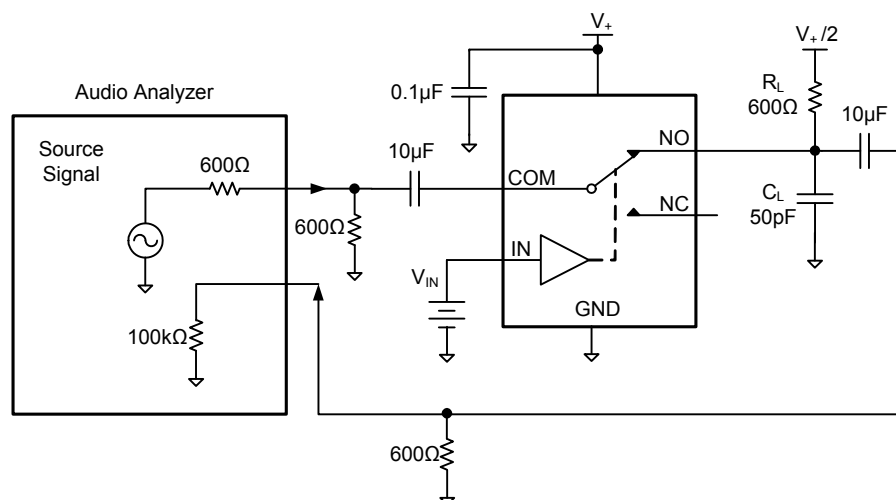
TEST CIRCUITS (Cont.)



Test Circuit 6. -3dB Bandwidth



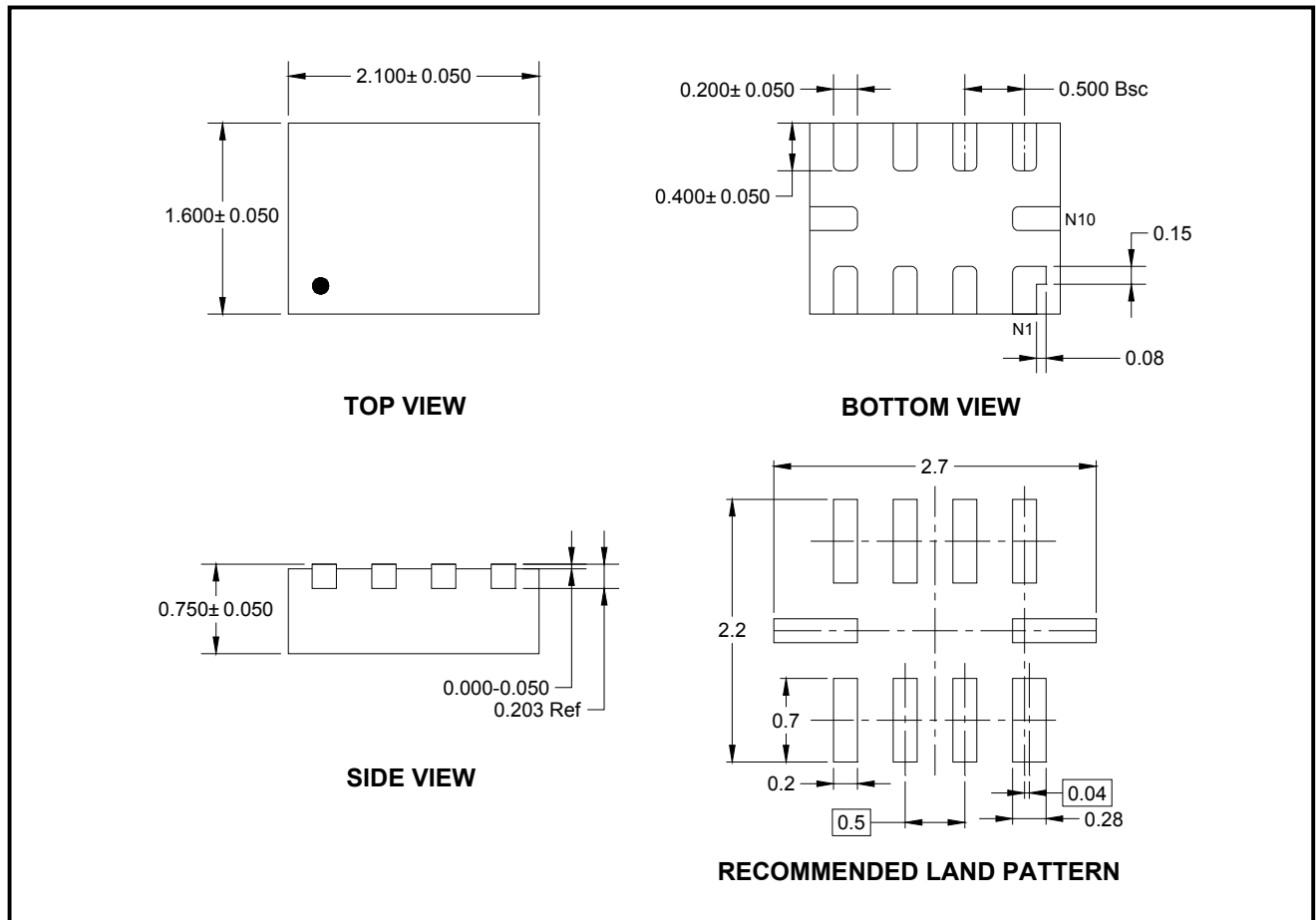
Test Circuit 7. Charge Injection (Q)



Test Circuit 8. Total Harmonic Distortion

PACKAGE OUTLINE DIMENSIONS

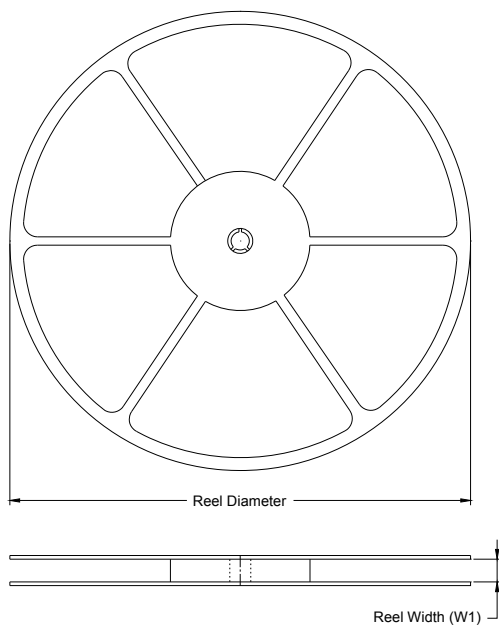
TQFN-2.1×1.6-10L



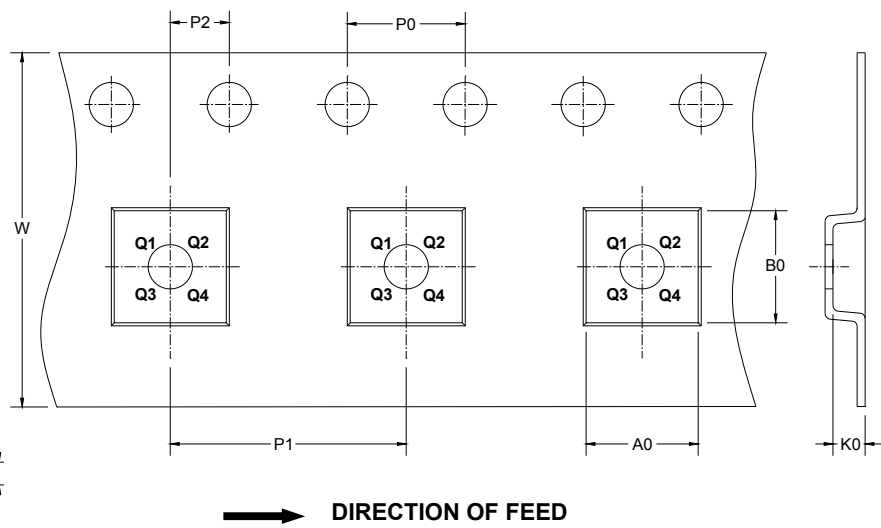
NOTE: All linear dimensions are in millimeters.

TAPE AND REEL INFORMATION

REEL DIMENSIONS



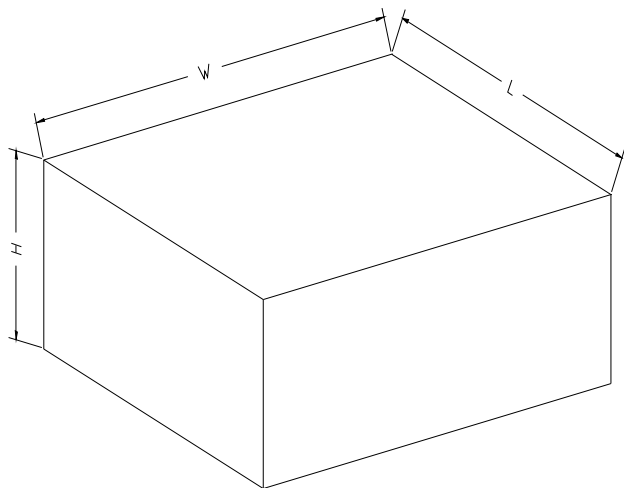
TAPE DIMENSIONS



NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF TAPE AND REEL

Package Type	Reel Diameter	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	P1 (mm)	P2 (mm)	W (mm)	Pin1 Quadrant
TQFN-2.1×1.6-10L	7"	9.0	1.9	2.3	0.9	4.0	4.00	2.0	8.0	Q1

CARTON BOX DIMENSIONS

NOTE: The picture is only for reference. Please make the object as the standard.

KEY PARAMETER LIST OF CARTON BOX

Reel Type	Length (mm)	Width (mm)	Height (mm)	Pizza/Carton
7" (Option)	368	227	224	8
7"	442	410	224	18